

### **3 A Schottky Barrier Rectifier**

### DESCRIPTION

This UPS360e3 in the Powermite3<sup>®</sup> package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3<sup>®</sup> package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

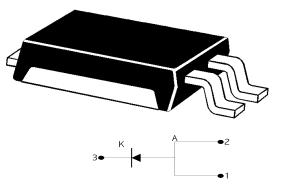
#### IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)					
Rating	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	60	v		
RMS Reverse Voltage	V <sub>R (RMS)</sub>	42	V		
Average Rectified Output Current	Ι <sub>ο</sub>	3	А		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load	I <sub>FSM</sub>	100 @ 25°C 50 @ 100°C	А		
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C		
Junction Temperature	TJ	-55 to +125	°C		

### THERMAL CHARACTERISTICS

Thermal Resistance					
Junction-to-case (bottom)	R <sub>θJC</sub>	3.2	°C/ Watt		
Junction to ambient (1)	R <sub>0JA</sub>	65	°C/ Watt		
(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print					

#### Powermite 3<sup>™</sup>



### **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
  Guard-ring-die construction for transient
- protection
  Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

#### **APPLICATIONS/BENEFITS**

- Switching and Regulating Power Supplies.Silicon Schottky (hot carrier) rectifier for
- minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low  ${\sf I}_{\sf RM}$
- Small foot print
   190 X 270 mils (1:1 Actual size)
  - See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

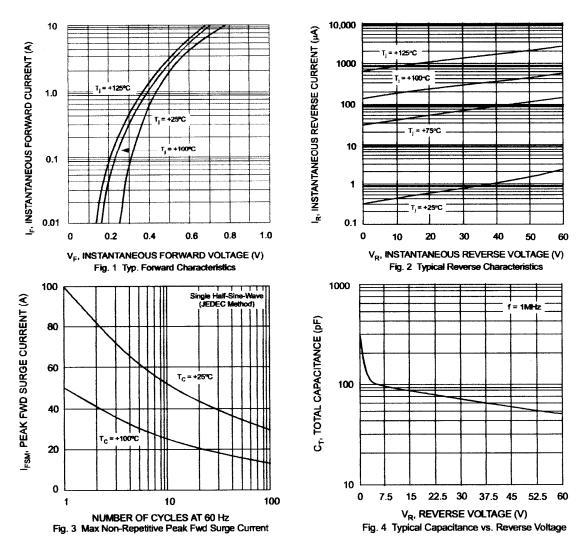
- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S360•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel



## **3 A Schottky Barrier Rectifier**

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Forward Voltage (Note 1)		I <sub>F</sub> = 3.5 A , T <sub>j</sub> =25 °C		0.59	0.63	
	VF	I <sub>F</sub> = 3.5 A , T <sub>j</sub> =125 °C		0.53	0.57	v
	VF	$I_{F} = 7 \text{ A}, T_{i} = 25 \text{ °C}$		0.72	0.76	v
		I <sub>F</sub> = 7 A , T <sub>j</sub> =25 °C		0.63	0.67	
Reverse Break Down Voltage (Note 1)	V <sub>BR</sub>	I <sub>R</sub> = 0.2 mA	60			V
Reverse Current (Note 1)		V <sub>R</sub> = 60V, T <sub>j</sub> = 25 °C		2	200	μA
	I <sub>R</sub>	V <sub>R</sub> = 60V, T <sub>j</sub> =100 °C		0.6	20	mA
		V <sub>R</sub> = 60V, T <sub>j</sub> =125 °C		2.5	150	mA
Capacitance	Ст	$V_{\rm R} = 4 \text{ V: } \text{f} = 1 \text{ MH}_2$		130		pF

Note: 1 Short duration test pulse used to minimize self-heating effect.

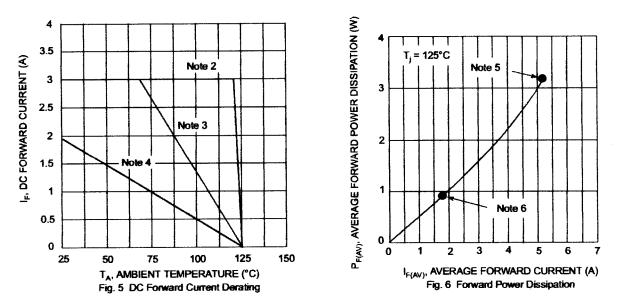


Microsemi

UPS360e3

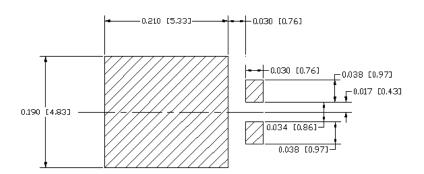


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- Notes: 2.  $T_A = T_{SOLDERING POINT,} R_{\Theta JS} = 3.2^{\circ} C/W R_{\Theta SA} = 0^{\circ} C/W.$ 3. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R<sub>OJA</sub> in range of 20-40° C/W.
  - 4. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta,JA}$  in range of 65° C/W. See mounting pad below.
  - 5. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 3.

#### PAD LAYOUT inches [mm]

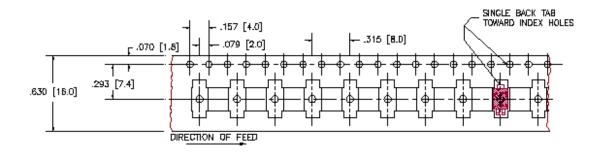


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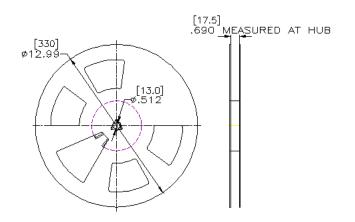


## **3 A Schottky Barrier Rectifier**

16 mm TAPE



13 INCH REEL

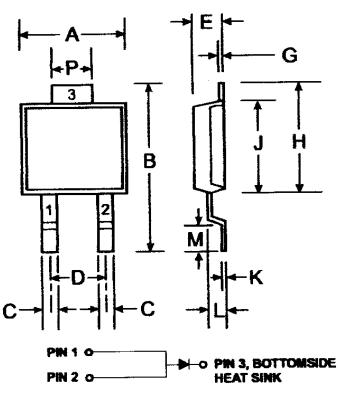


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### PACKAGE & MOUNTING PAD DIMENSIONS



POWERMITE®3			
Dim	Min Max		
•	4.03	4.09	
B	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
Ε	1.10	1.14	
G	.178 NOM		
Н	5.01	5.17	
J	4.37	4.43	
К	.178 NOM		
L	.71	.77	
M	.36	.46	
Р	1.73	1.83	
All Dimensions in mm			

Note: Pins 1 & 2 must be electrically connected at the printed circuit board.